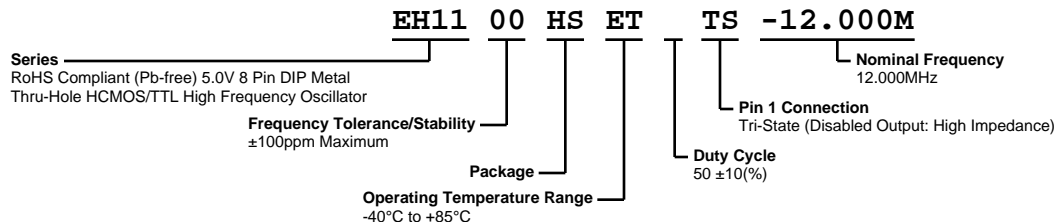


EH1100HSETTS-12.000M



ELECTRICAL SPECIFICATIONS

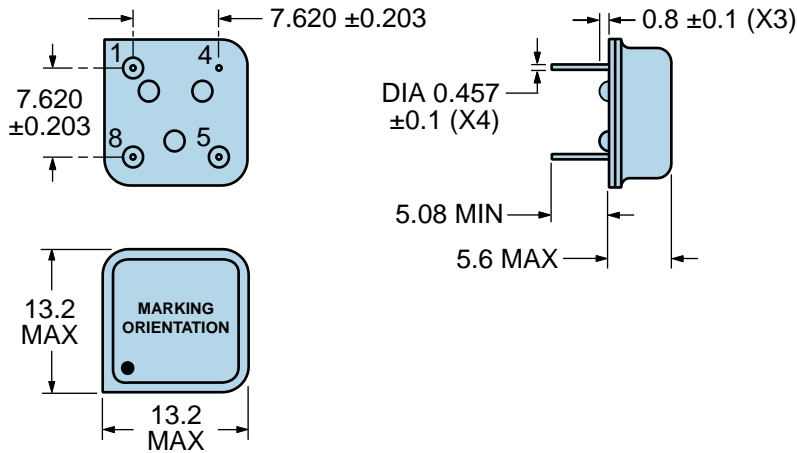
Nominal Frequency	12.000MHz
Frequency Tolerance/Stability	± 100 ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C , Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C , Shock, and Vibration.)
Aging at 25°C	± 5 ppm/year Maximum
Operating Temperature Range	-40°C to $+85^{\circ}\text{C}$
Supply Voltage	5.0Vdc $\pm 10\%$
Input Current	50mA Maximum (No Load)
Output Voltage Logic High (Voh)	2.4Vdc Minimum with TTL Load, Vdd-0.4Vdc Minimum with HCMOS Load (IOH = -16mA)
Output Voltage Logic Low (Vol)	0.4Vdc Maximum with TTL Load, 0.5Vdc Maximum with HCMOS Load (IOL = +16mA)
Rise/Fall Time	6nSec Maximum (Measured at 0.8Vdc to 2.0Vdc with TTL Load; Measured at 20% to 80% of waveform with HCMOS Load)
Duty Cycle	$50 \pm 10\%$ (Measured at 1.4Vdc with TTL Load or at 50% of waveform with HCMOS Load)
Load Drive Capability	10TTL Load or 50pF HCMOS Load Maximum
Output Logic Type	CMOS
Pin 1 Connection	Tri-State (Disabled Output: High Impedance)
Tri-State Input Voltage (Vih and Vil)	+2.2Vdc Minimum to enable output, +0.8Vdc Maximum to disable output (High Impedance), No Connect to enable output.
Absolute Clock Jitter	± 250 pSec Maximum, ± 100 pSec Typical
One Sigma Clock Period Jitter	± 50 pSec Maximum, ± 30 pSec Typical
Start Up Time	10mSec Maximum
Storage Temperature Range	-55°C to $+125^{\circ}\text{C}$

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

Fine Leak Test	MIL-STD-883, Method 1014, Condition A
Gross Leak Test	MIL-STD-883, Method 1014, Condition C
Lead Integrity	MIL-STD-883, Method 2004
Mechanical Shock	MIL-STD-202, Method 213, Condition C
Resistance to Soldering Heat	MIL-STD-202, Method 210
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, Method 1010
Vibration	MIL-STD-883, Method 2007, Condition A

EH1100HSETTS-12.000M

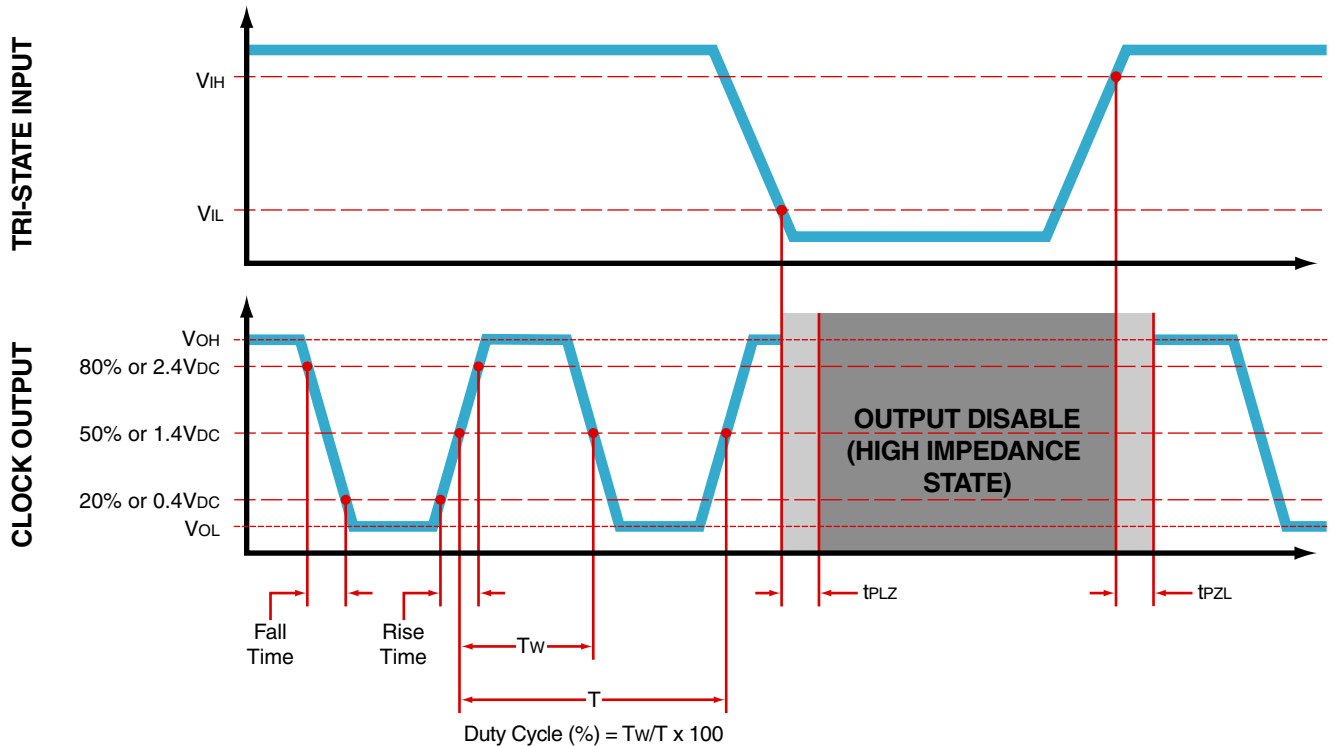
MECHANICAL DIMENSIONS (all dimensions in millimeters)



PIN	CONNECTION
1	Tri-State
4	Case/Ground
5	Output
8	Supply Voltage

LINE	MARKING
1	ECLIPTEK
2	EH11TS EH11=Product Series
3	12.000M
4	XXYYZ XX=Ecliptek Manufacturing Code Y=Last Digit of the Year ZZ=Week of the Year

OUTPUT WAVEFORM & TIMING DIAGRAM

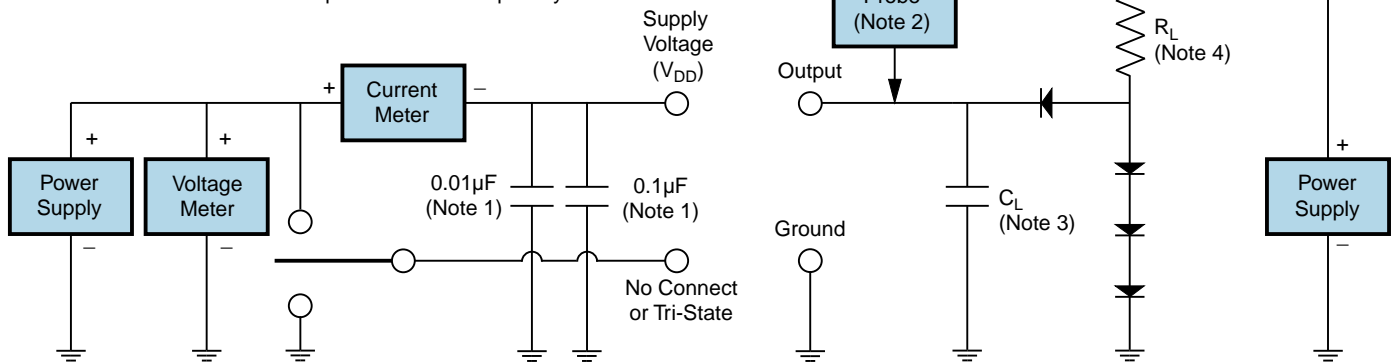


EH1100HSETTS-12.000M

Test Circuit for TTL Output

Output Load Drive Capability	R _L Value (Ohms)	C _L Value (pF)
10TTL	390	15
5TTL	780	15
2TTL	1100	6
10LSTTL	2000	15
1TTL	2200	3

Table 1: R_L Resistance Value and C_L Capacitance Value Vs. Output Load Drive Capability



Note 1: An external 0.1µF low frequency tantalum bypass capacitor in parallel with a 0.01µF high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.

Note 4: Resistance value R_L is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.

Note 5: All diodes are MMBD7000, MMBD914, or equivalent.

EH1100HSETTS-12.000M

Test Circuit for CMOS Output



Note 1: An external $0.1\mu\text{F}$ low frequency tantalum bypass capacitor in parallel with a $0.01\mu\text{F}$ high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance ($<12\text{pF}$), 10X attenuation factor, high impedance ($>10\text{Mohms}$), and high bandwidth ($>300\text{MHz}$) passive probe is recommended.

Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.

Recommended Solder Reflow Methods



High Temperature Solder Bath (Wave Solder)

T_S MAX to T_L (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (T_S MIN)	150°C
- Temperature Typical (T_S TYP)	175°C
- Temperature Maximum (T_S MAX)	200°C
- Time (t_s MIN)	60 - 180 Seconds
Ramp-up Rate (T_L to T_P)	3°C/second Maximum
Time Maintained Above:	
- Temperature (T_L)	217°C
- Time (t_L)	60 - 150 Seconds
Peak Temperature (T_P)	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T_P Target)	250°C +0/-5°C
Time within 5°C of actual peak (t_p)	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1

EH1100HSETTS-12.000M

Recommended Solder Reflow Methods



Low Temperature Infrared/Convection 185°C

T_S MAX to T_L (Ramp-up Rate) 5°C/second Maximum

Preheat

- Temperature Minimum (T_S MIN) N/A
- Temperature Typical (T_S TYP) 150°C
- Temperature Maximum (T_S MAX) N/A
- Time (t_s MIN) 60 - 120 Seconds

Ramp-up Rate (T_L to T_P) 5°C/second Maximum

Time Maintained Above:

- Temperature (T_L) 150°C
- Time (t_L) 200 Seconds Maximum

Peak Temperature (T_P) 185°C Maximum

Target Peak Temperature (T_P Target) 185°C Maximum 2 Times

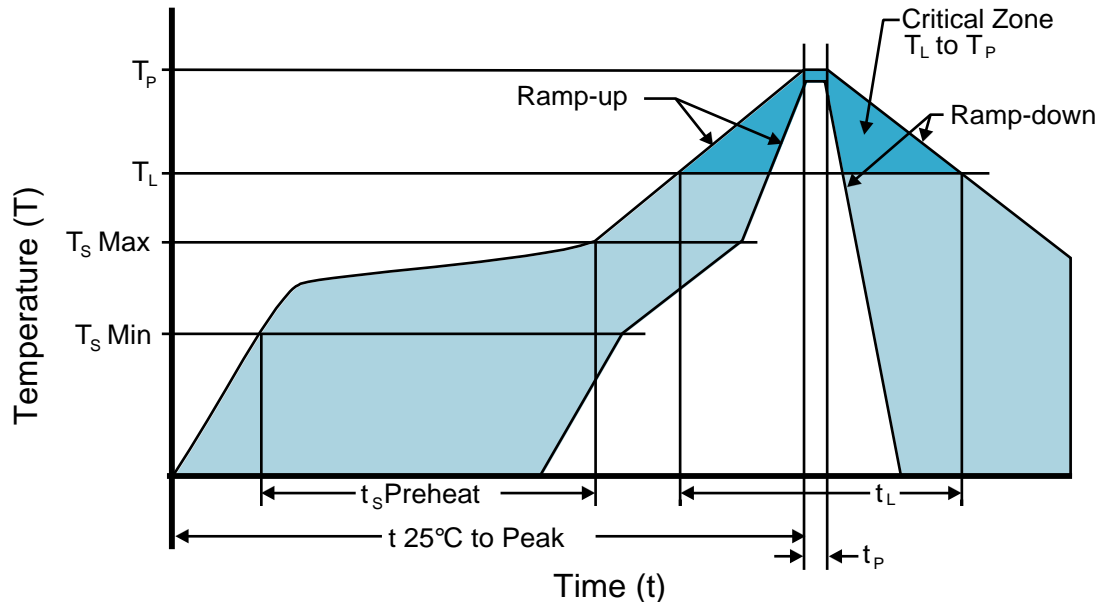
Time within 5°C of actual peak (t_p) 10 seconds Maximum 2 Times

Ramp-down Rate 5°C/second Maximum

Time 25°C to Peak Temperature (t) N/A

Moisture Sensitivity Level Level 1

Recommended Solder Reflow Methods



Low Temperature Solder Bath (Wave Solder)

$T_s \text{ MAX}$ to T_L (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum ($T_s \text{ MIN}$)	N/A
- Temperature Typical ($T_s \text{ TYP}$)	150°C
- Temperature Maximum ($T_s \text{ MAX}$)	N/A
- Time ($t_s \text{ MIN}$)	30 - 60 Seconds
Ramp-up Rate (T_L to T_p)	5°C/second Maximum
Time Maintained Above:	
- Temperature (T_L)	150°C
- Time (t_L)	200 Seconds Maximum
Peak Temperature (T_p)	245°C Maximum
Target Peak Temperature ($T_p \text{ Target}$)	245°C Maximum 1 Time / 235°C Maximum 2 Times
Time within 5°C of actual peak (t_p)	5 seconds Maximum 1 Time / 15 seconds Maximum 2 Times
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum.

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum.